

CLAIMS

1. A ceramic heater wherein a heating element is arranged on a surface of a ceramic substrate or inside the ceramic substrate,
- 5 the surface roughness R_{max} of the side face of said ceramic substrate being from 0.1 to 200 μm according to JIS B 0601.
- 10 2. The ceramic heater according to claim 1, wherein said surface roughness R_{max} is from 0.5 to 200 μm according to JIS B 0601.
3. The ceramic heater according to claim 1 or 2, wherein said ceramic substrate is fitted into a supporting case.
- 15 4. The ceramic heater according to any of claims 1 to 3, wherein said ceramic substrate is made of a nitride ceramic.
- 20 5. The ceramic heater according to any of claims 1 to 3, wherein said ceramic substrate is made of a carbide ceramic or an oxide ceramic.
6. The ceramic heater according to any of claims 1 to 5,
- 25 wherein said ceramic heater is for heating a semiconductor wafer.
7. The ceramic heater according to any of claims 1 to 6, wherein the thickness of said ceramic substrate is over 1.5 mm.